





# AFGH4L25T120RWD

## ELECTRICAL CHARACTERISTICS ( $T_J = 25\text{ C}$ unless otherwise specified) (continued)

| Parameter                        | Symbol       | Test Conditions   | Min | Typ  | Max | Unit |
|----------------------------------|--------------|---|-----|------|-----|------|
| <b>SWITCHING CHARACTERISTICS</b> |              |   |     |      |     |      |
| Turn-On Delay Time               | $t_{d(on)}$  | $V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V},$<br>$I_C = 12.5\text{ A}, R_G = 8\ \Omega,$<br>$T_J = 175\text{ C}$ | -   | 42.5 | -   | ns   |
| Turn-Off Delay Time              | $t_{d(off)}$ |   | -   | 348  | -   |      |
| Rise Time                        | $t_r$        |   | -   | 27.4 | -   |      |
| Fall Time                        | $t_f$        |   | -   | 384  | -   |      |
| Turn-                            |              |   |     |      |     |      |

# AFGH4L25T120RWD

## TYPICAL CHARACTERISTICS

Figure 1. Output Characteristics

Figure 2. Output Characteristics

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## TYPICAL CHARACTERISTICS

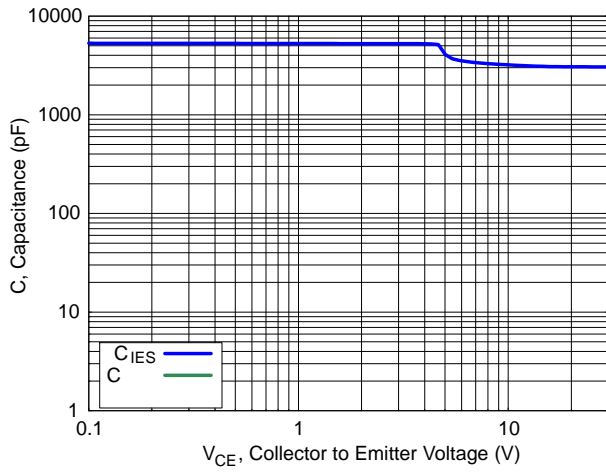


Figure 7. Capacitance Characteristics

Figure 8. Gate Charge Characteristics

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## TYPICAL CHARACTERISTICS

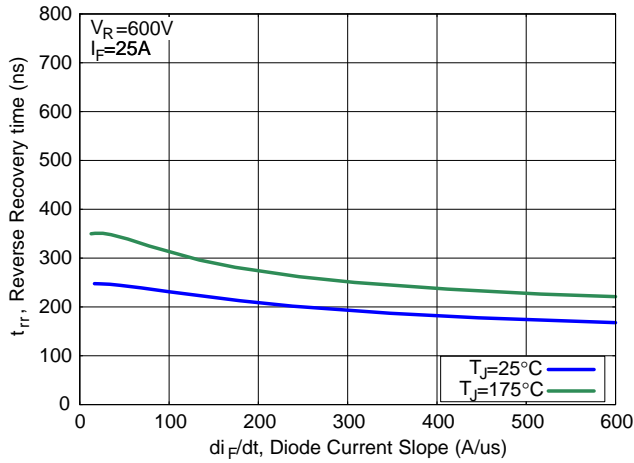


Figure 19. Diode Reverse Recovery Time

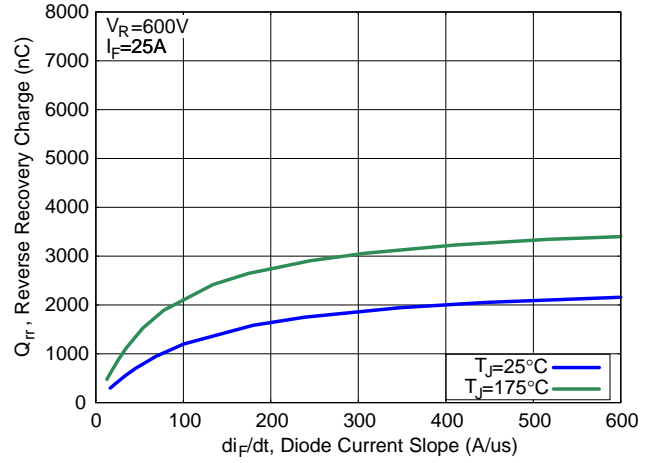


Figure 20. Diode Stored Charge Characteristics

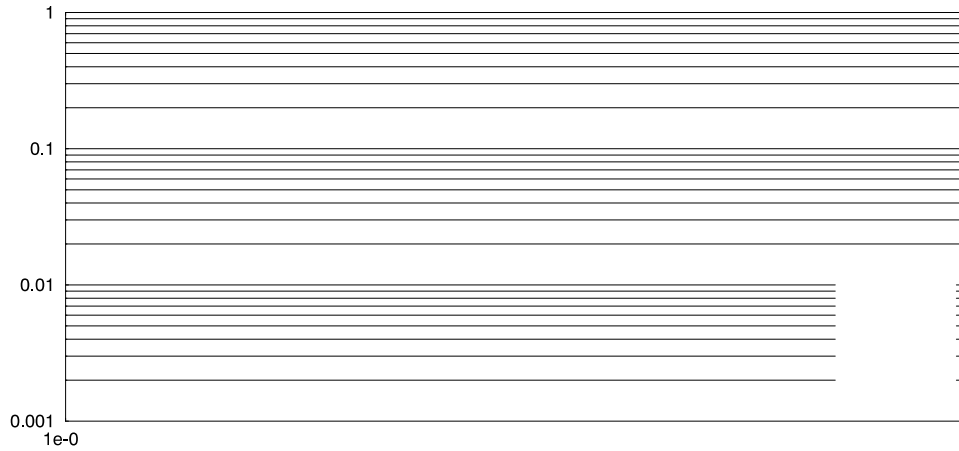


Figure 21. Transient Thermal Impedance of IGBT





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